

NCE P-Channel **Super Trench** Power MOSFET

Description

The NCEP40P60G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

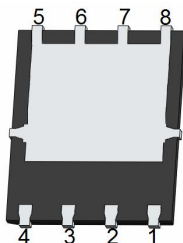
- $V_{DS} = -40V, I_D = -60A$
 $R_{DS(on)} = 8.8m\Omega$ (typical) @ $V_{GS} = -10V$
 $R_{DS(on)} = 12.5m\Omega$ (typical) @ $V_{GS} = -4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔV_{ds} TESTED!

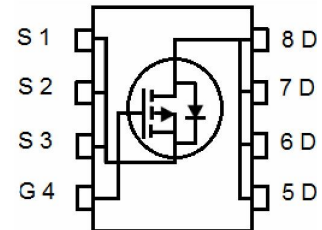
DFN 5X6



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P40P60G	NCEP40P60G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	$I_D(T_c=25^\circ\text{C})$	-60	A
Drain Current-Continuous($T_c=100^\circ\text{C}$)	$I_D(T_c=100^\circ\text{C})$	-42	A
Pulsed Drain Current	I_{DM}	-240	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	$P_D(T_c=25^\circ\text{C})$	80	W
Derating factor		0.64	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 1)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.56	$^\circ\text{C/W}$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.1	-1.7	-2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	8.8	11.0	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	12.5	17.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	-	30	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, F=1.0MHz	-	2450	-	PF
Output Capacitance	C _{oss}		-	660	-	PF
Reverse Transfer Capacitance	C _{rss}		-	18	-	PF
Switching Characteristics <small>(Note 2)</small>						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-20V, I _D =-20A V _{GS} =-10V, R _G =1.6Ω	-	9	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Q _g	V _{DS} =-20V, I _D =-20A, V _{GS} =-10V	-	39	-	nC
Gate-Source Charge	Q _{gs}		-	7.8		nC
Gate-Drain Charge	Q _{gd}		-	5.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A	-		-1.2	V
Diode Forward Current	I _S		-	-	-60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A	-	22		nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs	-	58		nC

Notes:

1. EAS condition : T_J=25°C, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_G=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_J(MAX)=150°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

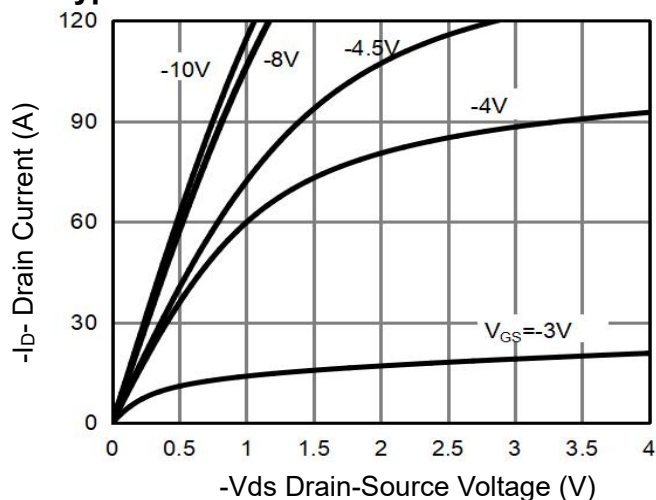


Figure 1 Output Characteristics

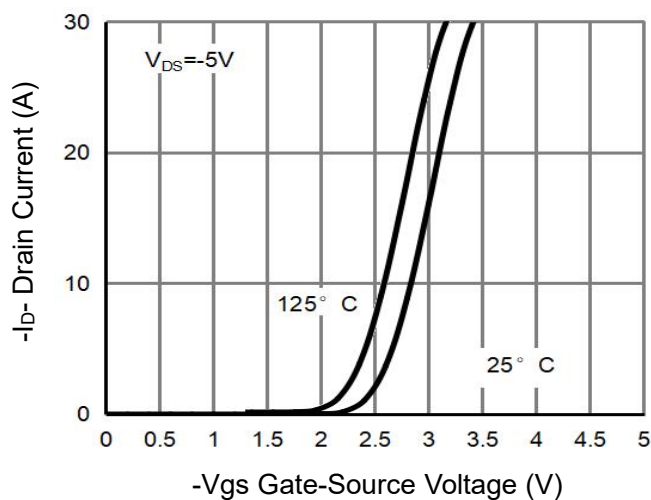


Figure 2 Transfer Characteristics

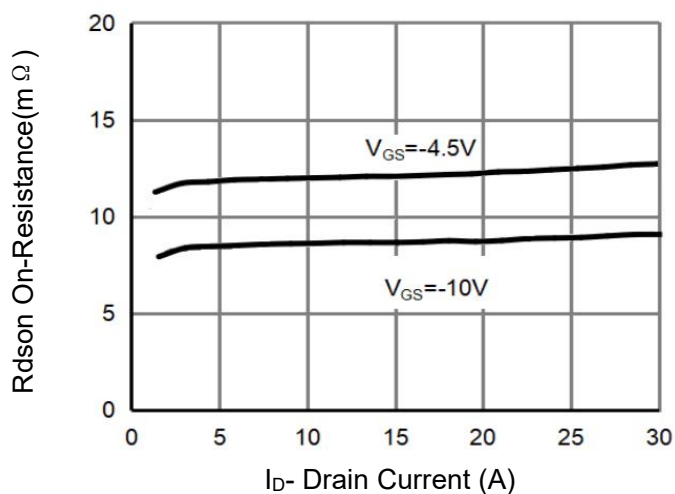


Figure 3 R_DS(on) vs I_D

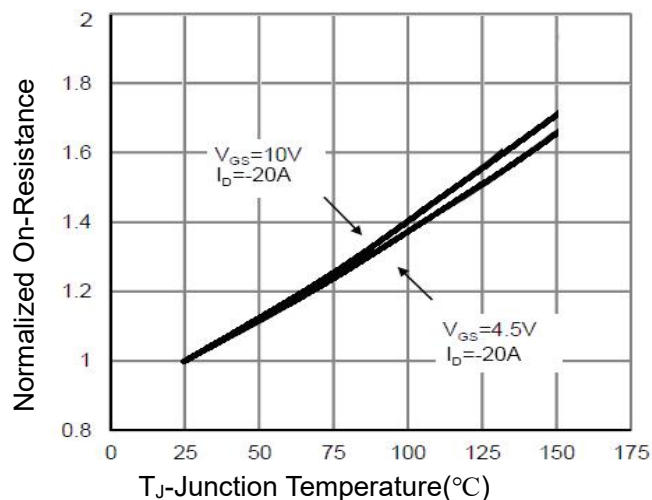


Figure 4 R_DS(on) vs T_J

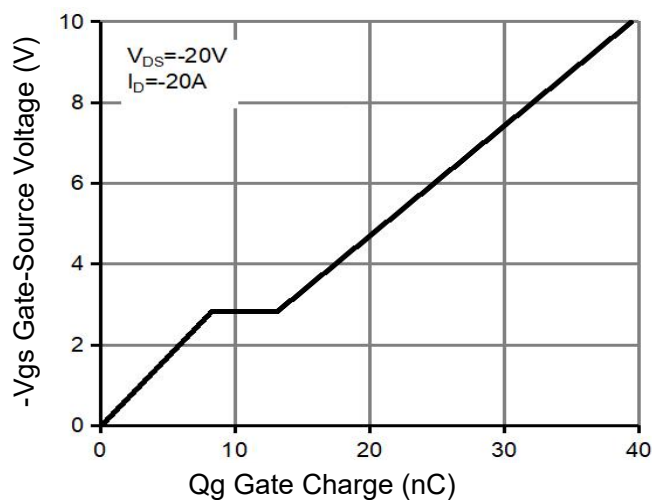


Figure 5 Gate Charge

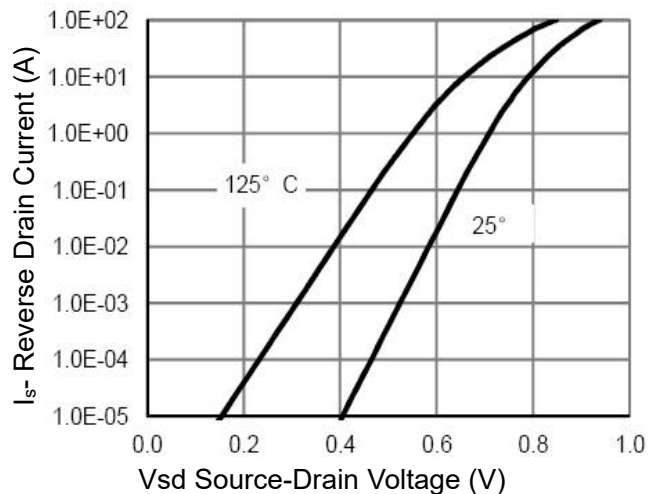


Figure 6 Source-Drain Diode Forward

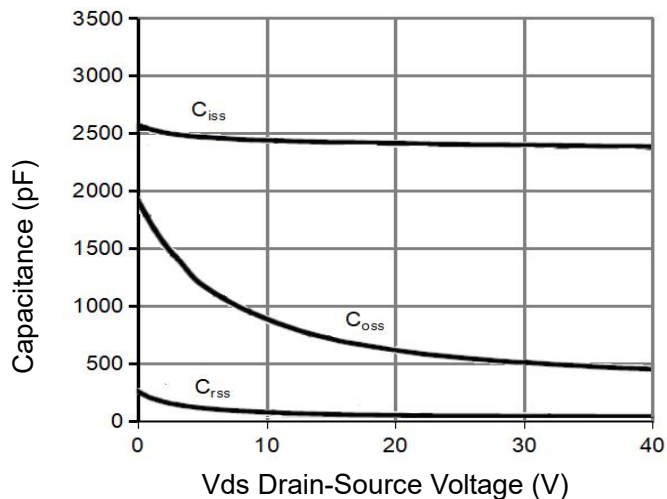


Figure 7 Capacitance vs Vds

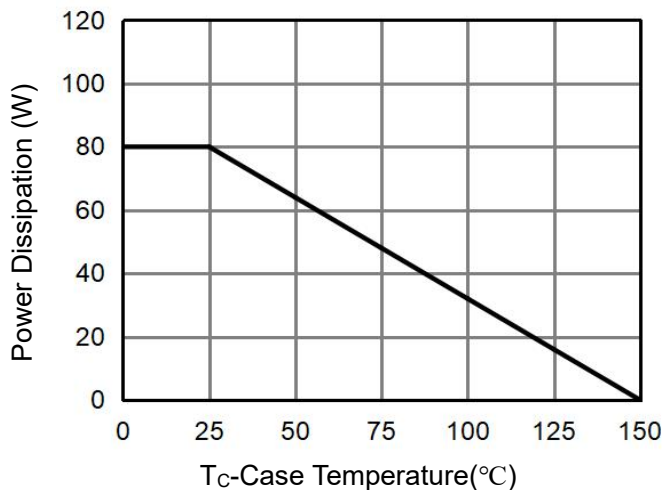


Figure 9 Power De-rating

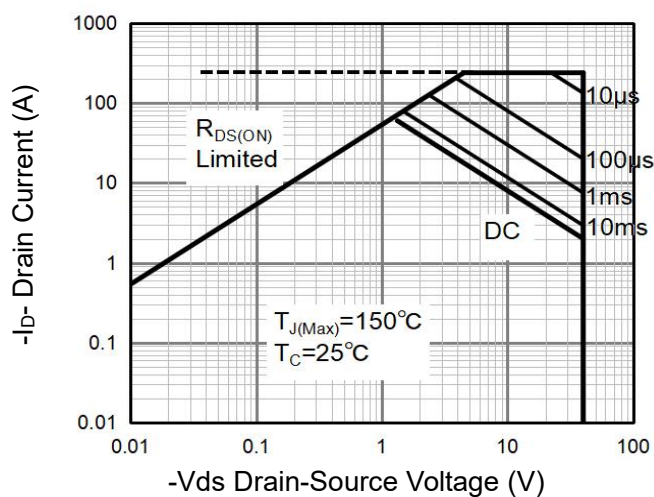


Figure 8 Safe Operation Area (Note3)

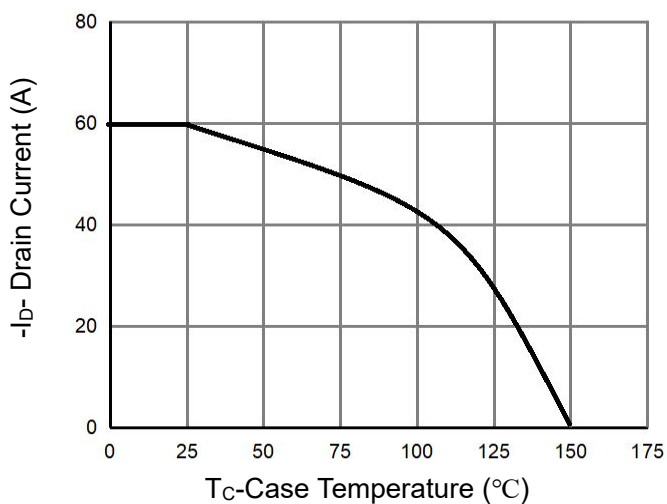


Figure 10 Current De-rating

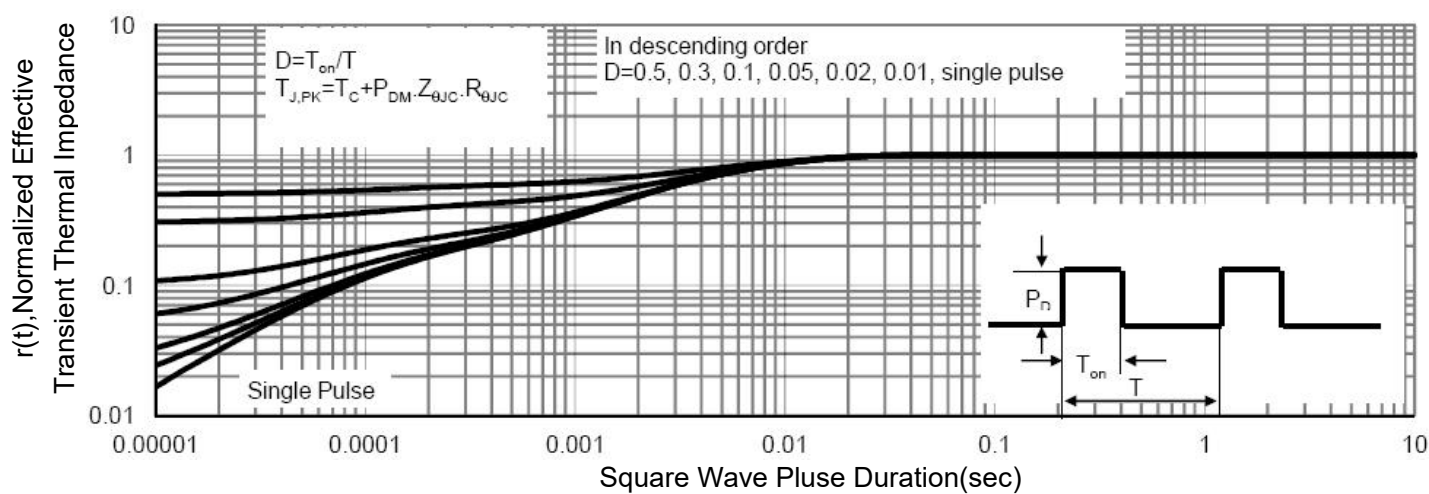
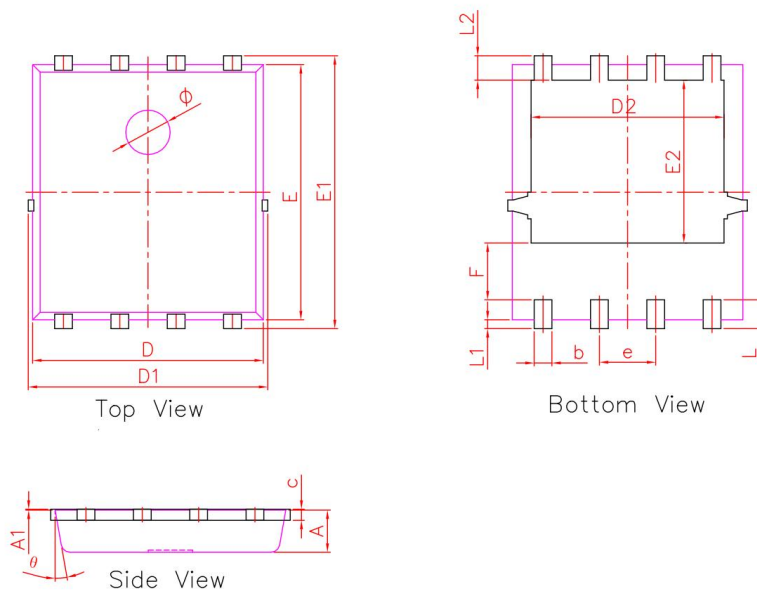


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



PDFN5X6-8L			
DIM.	MIN.	NOM.	MAX.
A	0.90	0.95	1.00
A1	0.00	0.02	0.05
b	0.35	0.40	0.50
c	0.20	0.25	0.30
D	5.10	5.20	5.30
D1	5.10	5.40	5.50
D2	4.25	4.35	4.45
e	1.27 BSC		
E	5.70	5.75	5.80
E1	6.00	6.15	6.30
E2	3.57	3.67	3.77
F	1.18	1.28	1.38
L	0.55	0.65	0.75
L1	0.15	0.20	0.25
L2	0.45	0.55	0.65
φ	0.90	1.00	1.10
Θ	8°	10°	12°
All dimensions in millimeters			

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